

Shuttle Process	Technology	Tape-In Date TWN Time							
		January	February	March	April	May	June		
5nm	Logic, Fin FET (FF) (0.75/1.2V)		Feb		Apr				
6nm	Logic, Fin FET (0.75/1.8V)				Apr				
7nm	Logic, Fin FET (0.75/1.8V)			Mar			Jun		
16nm	Logic, FinFET Compact (0.8/1.8V)		Feb		Apr		Jun		
	Logic, FinFET Compact Plus (0.8/1.8V)								
	Logic, FinFET Plus (0.8/1.8V)								
28nm	Logic, HPM (0.9/1.8V, 0.9/2.5V)	Jan-13	Feb-19	Mar-17	Apr-7	May-12	Jun-16		
	Logic, HPC (0.9/1.8V, 0.9/2.5V)								
	Logic, HPC Plus (0.9/1.8V, 0.9/2.5V)								
	Logic, HP (0.85/1.8V, 0.85/2.5V)								
	Logic, LP (1.05/1.8V, 1.05/2.5V)								
	Logic, HPL (1.0 & 1.8V, 1.0/2.5V)								
	RF HPC Plus (0.9/1.8V, 0.9/2.5V)								
	RF HPC (0.9/1.8V, 0.9/2.5V)								
	RF LP (1.05V/1.8V)								
28nm	High Voltage (0.9/8/25/28V)		Feb-24						
	Logic, 40LP (1.1/1.8V, 1.1/2.5V)		Feb-23	Mar-16	Apr-13	May-11	Jun-15		
Logic, 40LP Plus (1.1/2.5V)									
Logic, 40ULP (1.1/2.5V, 0.9/2.5V)									
Mixed-Signal/RF, 40LP (1.1/1.8V, 1.1/2.5V)									
Mixed-Signal/RF, 40ULP (1.1/2.5V, 0.9/1.8V, 0.9/2.5V)									
Logic, 45GS (45GS = 40G) (0.9/1.8V, 0.9/2.5V)									
High Voltage (1.1/5/6/25/32V)									
High Voltage (1.1/8/25V)									
ReRAM, RF 40ULP (0.9V/2.5V)									
40nm LP & 45nm GS (45GS = 40G)	EmbFlash, 40LP (1.1/2.5V)		Feb-23		Apr-13		Jun-15		
	EmbFlash, 40ULP (0.9V/2.5V)								
65nm	Logic, LP/DGO (1.2/2.5V, 1.2/3.3V)	Jan-6	Feb-17	Mar-17		May-5	Jun-9		
	Logic, GP/DGO (1.0/1.8V, 1.0/2.5V, 1.0/3.3V)								
	Logic, LP-based TGO (1.0/1.2/2.5V)								
	Logic, ULP (1.0/2.5V)								
	Mixed-Signal/RF, GP (1.0/2.5V)	Jan-6				Mar-17			May-5
.18um	Mixed-Signal/RF, LP (1.2/2.5V)			Mar-3	Apr-7	May-5	Jun-2		
	Mixed-Signal/RF, G (1.8/3.3V)	Jan-6							
	Mixed-signal/RF, G (1.8/3.3V) embedded MTP								
	Mixed-signal/RF, G (1.8/3.3V) embedded OTP (Kilopass/eMemory)								
	Mixed Signal, G, (1.8/5V)				Apr-7			Jun-2	
	Logic, G (1.8/3.3V)			Mar-3					
	Logic, G (1.8/3.3V), Embedded OTP/MTP	Jan-6							
	Logic, LV (1.5/3.3V)						Jun-2		
	Logic, LP (1.8/3.3V)			Mar-3	Apr-7	May-5			
	SiGe BiCMOS, G (1.8/3.3V)	Jan-6							
	EmbFlash (1K, 20K) (1.8/3.3V)						Jun-2		
	EmbFlash Enhanced (1.8/3.3V)								
	EmbFlash Enhanced (1.8/5V)								
	EmbFlash HDR (1.8/3.3V)								
	EmbFlash eLL (1.8/3.3V)								
	High Voltage (1.8/3.3/32V)					May-5			
	High Voltage (1.8/5/32V)								
	High Voltage, BCD (Generation-2)			Mar-3	Apr-7				
	High Voltage, BCD (Generation-3)								
	Part 1	Mixed-Signal/RF, G (1.8/3.3V)	Jan-13		Mar-10	Apr-21	May-12	Jun-9	
Mixed-Signal/RF, G (1.8/3.3V) embedded MTP									
Mixed-Signal/RF, G (1.8/3.3V) embedded OTP (Kilopass/eMemory)									
Mixed Signal, G, (1.8/5V)						Apr-21	May-12		
Logic, G (1.8/3.3V)									
Logic, G (1.8/3.3V), Embedded OTP/MTP									
Logic, LV (1.5/3.3V)							Apr-21		May-12
Logic, LP (1.8/3.3V)							Mar-10		
EmbFlash (1K, 20K) (1.8/3.3V)									
EmbFlash Enhanced (1.8/3.3V)		Jan-13							Apr-21
Part 2	EmbFlash Enhanced (1.8/5V)								
	EmbFlash HDR (1.8/3.3V)								
	EmbFlash eLL (1.8/3.3V)								
	High Voltage (1.8/3.3/32V)								
	High Voltage (1.8/5/32V)								
	High Voltage, BCD (Generation-2)			Mar-10					
	High Voltage, BCD (Generation-3)					May-12	Jun-9		
	Part 3	Mixed-Signal/RF, G (1.8/3.3V)	Jan-20		Mar-24		May-26		
		Mixed-Signal/RF, G (1.8/3.3V) embedded MTP							
		Mixed-Signal/RF, G (1.8/3.3V) embedded OTP (Kilopass/eMemory)							
Mixed Signal, G, (1.8/5V)									
Logic, G (1.8/3.3V)									
Logic, G (1.8/3.3V), Embedded OTP/MTP							Mar-24		May-26
Logic, LV (1.5/3.3V)									
Logic, LP (1.8/3.3V)		Jan-20							
EmbFlash (1K, 20K) (1.8/3.3V)									
EmbFlash Enhanced (1.8/3.3V)									
Part 3	EmbFlash Enhanced (1.8/5V)								
	EmbFlash HDR (1.8/3.3V)								
	EmbFlash eLL (1.8/3.3V)								
	High Voltage (1.8/3.3/32V)								
	High Voltage (1.8/5/32V)								
	High Voltage, BCD (Generation-2)	Jan-20		Mar-24		May-26			
High Voltage, BCD (Generation-3)									